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# AAP Gen 7 (TO-240AA) Power Modules Thyristor/Diode and Thyristor/Thyristor, 105 A



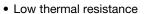
PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub> or I <sub>F(AV)</sub>	105 A				
Type	Modules - thyristor, standard				
Package	AAP Gen 7 (TO-240AA)				

#### **MECHANICAL DESCRIPTION**

The AAP Gen 7 (TO-240AA), new generation of APP module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

#### **FEATURES**

- High voltage
- Industrial standard package



- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **BENEFITS**

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- · High surge capability
- · Easy mounting on heatsink

#### **ELECTRICAL DESCRIPTION**

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
I <sub>T(AV)</sub> or I <sub>F(AV)</sub>	85 °C	105				
I <sub>O(RMS)</sub>	As AC switch	235	Λ			
I <sub>TSM,</sub>	50 Hz	2000	А			
I <sub>FSM</sub>	60 Hz	2094				
l <sup>2</sup> t	50 Hz	20	kA <sup>2</sup> s			
I-I	60 Hz	18.26	KA-S			
I <sup>2</sup> √t		200	kA²√s			
V <sub>DRM</sub> /V <sub>RRM</sub>	Range	400 to 1600	V			
T <sub>Stg</sub>		-40 to +130	%0			
T <sub>J</sub>		-40 to +130	°C			

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#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I <sub>RRM,</sub> I <sub>DRM</sub> AT 130 °C mA			
	04	400	500	400				
	06	600	700	600				
	08	800	900	800				
VS-VSK.105	10	1000	1100	1000	20			
	12	1200	1300	1200				
	14	1400	1500	1400				
	16	1600	1700	1600				

ON-STATE CONDUCTION	OVA ADC:		TEOT OO!	TIONIO	VALUES	LINUTC
PARAMETER	SYMBOL		TEST COND	HUNS	VALUES	UNITS
Maximum average on-state current (thyristors)	I <sub>T(AV)</sub>	Į.	180° conduction, half sine wave,		105	
Maximum average forward current (diodes)	I <sub>F(AV)</sub>	T <sub>C</sub> = 85 °C				
Maximum continuous RMS on-state current, as AC switch	I <sub>O(RMS)</sub>		or or I(RMS)			Α
		t = 10 ms	No voltage		2000	
Maximum peak, one-cycle non-repetitive	I <sub>TSM</sub>	t = 8.3 ms	reapplied	Sinusoidal	2094	
on-state or forward current	or I <sub>FSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	half wave, initial $T_J = T_J$ maximum	1682	
	·F3W	t = 8.3 ms	reapplied		1760	
		t = 10 ms	t = 10 ms No voltage	20		
Maximum I <sup>2</sup> t for fusing	12.	t = 8.3 ms	reapplied		18.26	kA <sup>2</sup> s
	l <sup>2</sup> t	t = 10 ms	100 % V <sub>RBM</sub>	Initial $T_J = T_J$ maximum	14.14	
		t = 8.3 ms	reapplied		12.91	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t <sup>(1)</sup>		t = 0.1 ms to 10 ms, no voltage reapplied $T_J = T_J$ maximum			kA²√s
Marian and a sulface ball allows	V (2)	Low level (3)	T <sub>J</sub> = T <sub>J</sub> maximum		0.98	
Maximum value or threshold voltage	V <sub>T(TO)</sub> (2)	High level (4)			1.12	V
Maximum value of on-state	(2)	Low level (3)	<b>-</b> - ·		2.7	
slope resistance	r <sub>t</sub> (2)	High level (4)	$T_J = T_J$ maximum		2.34	mΩ
	$V_{TM}$	$I_{TM} = \pi \times I_{T(AV)}$				.,
Maximum peak on-state or forward voltage	V <sub>FM</sub>	$I_{FM} = \pi \times I_{F(AV)}$	$T_J = 25  ^{\circ}C$		1.8	V
Maximum non-repetitive rate of rise of	dl/dt	$T_{\rm J} = 25~{\rm ^{\circ}C}$ , from 0.67 $V_{\rm DRM}$ ,		150	A/µs	
turned on current	ui/ut	$I_{TM} = \pi \times I_{T(AV)}$ , $I_g = 500$ mA, $t_r < 0.5 \mu s$ , $t_p > 6 \mu s$		130	Ανμο	
Maximum holding current	l <sub>Η</sub>	T <sub>J</sub> = 25 °C, anode supply = 6 V, resistive load, gate open circuit			250	mA
Maximum latching current	ΙL	$T_J = 25 ^{\circ}\text{C}$ , and	T <sub>J</sub> = 25 °C, anode supply = 6 V, resistive load			

#### Notes

<sup>(1)</sup>  $I^2t$  for time  $t_x = I^2\sqrt{t} \times \sqrt{t_x}$ 

<sup>&</sup>lt;sup>(2)</sup> Average power =  $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$ 

 $<sup>^{(3)}</sup>$  16.7 % x  $\pi$  x  $I_{AV}$  < I <  $\pi$  x  $I_{AV}$ 

<sup>(4)</sup>  $I > \pi \times I_{AV}$ 

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TRIGGERING						
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS	
Maximum peak gate power	$P_{GM}$			12	W	
Maximum average gate power	P <sub>G(AV)</sub>			3	VV	
Maximum peak gate current	I <sub>GM</sub>			3	А	
Maximum peak negative gate voltage	- V <sub>GM</sub>			10		
	V <sub>GT</sub>	T <sub>J</sub> = -40 °C	Anode supply = 6 V	4.0	V	
Maximum gate voltage required to trigger		T <sub>J</sub> = 25 °C		2.5		
		T <sub>J</sub> = 125 °C	- resistive load	1.7		
		T <sub>J</sub> = -40 °C		270		
Maximum gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	150	mA	
		T <sub>J</sub> = 125 °C	resistive load	80		
Maximum gate voltage that will not trigger	$V_{GD}$	T <sub>J</sub> = 125 °C, rated V <sub>DRM</sub> applied		0.25	V	
Maximum gate current that will not trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, rated V <sub>DRM</sub> applied		6	mA	

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak reverse and off-state leakage current at V <sub>RRM</sub> , V <sub>DRM</sub>	I <sub>RRM,</sub> I <sub>DRM</sub>	T <sub>J</sub> = 130 °C, gate open circuit	20	mA				
Maximum RMS insulation voltage	V <sub>INS</sub>	50 Hz	3000 (1 min) 3600 (1 s)	V				
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = 130 °C, linear to 0.67 V <sub>DRM</sub>	1000	V/µs				

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Junction operating temperature range		$T_J$		-40 to +130	°C		
Storage temperature range		T <sub>Stg</sub>		-40 10 +130	C		
Maximum internal thermal resistance, junction to case per leg		R <sub>thJC</sub>	DC operation	0.22	°C AM		
Typical thermal resistance, case to heatsink per module		R <sub>thCS</sub>	Mounting surface flat, smooth and greased	0.1	°C/W		
	to heatsink		A mounting compound is recommended and the torque should be rechecked after a period	4			
Mounting torque ± 10 % busbar			of 3 hours to allow for the spread of the compound.	3	Nm		
Approximate weight				75	g		
				2.7	OZ.		
Case style			JEDEC®	AAP Gen 7	(TO-240AA)		

△R CONDUCTION PER JUNCTION											
DEVICES	5	SINE HALF WAVE CONDUCTION					RECTANGULAR WAVE CONDUCTION				UNITS
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.105	0.04	0.048	0.063	0.085	0.125	0.033	0.052	0.067	0.088	0.127	°C/W

#### Note

Table shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

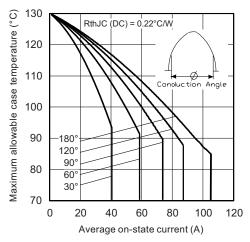


Fig. 1 - Current Ratings Characteristics

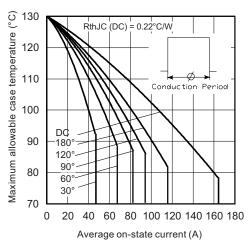


Fig. 2 - Current Ratings Characteristics

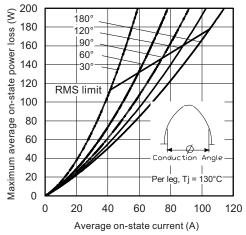


Fig. 3 - On-State Power Loss Characteristics

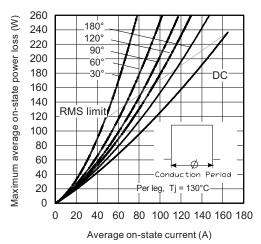
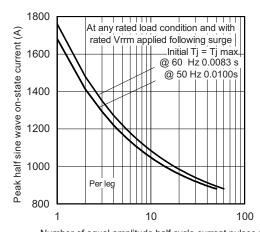


Fig. 4 - On-State Power Loss Characteristics



Number of equal amplitude half cycle current pulses (N)

Fig. 5 - Maximum Non-Repetitive Surge Current

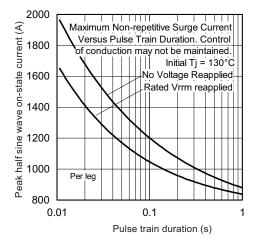


Fig. 6 - Maximum Non-Repetitive Surge Current

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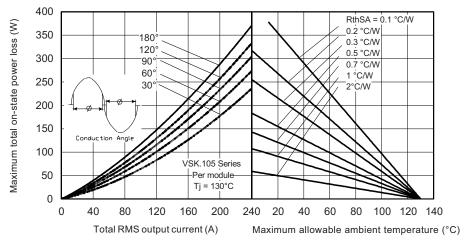


Fig. 7 - On-State Power Loss Characteristics

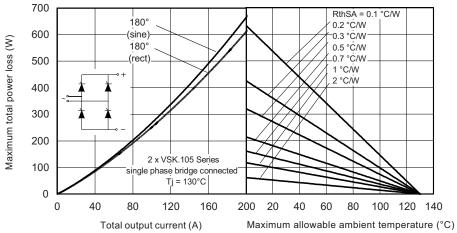


Fig. 8 - On-State Power Loss Characteristics

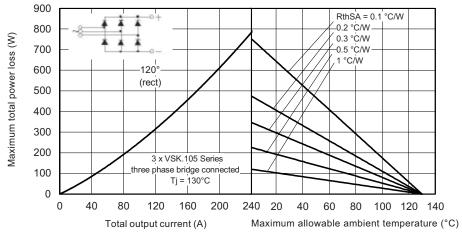


Fig. 9 - On-State Power Loss Characteristics

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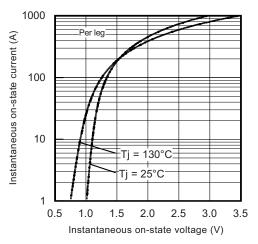


Fig. 10 - On-State Voltage Drop Characteristics

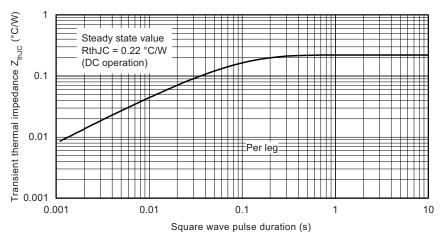


Fig. 11 - Thermal Impedance Z<sub>thJC</sub> Characteristics

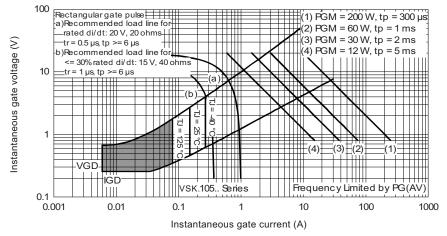
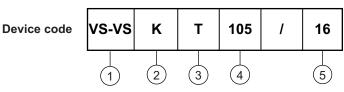


Fig. 12 - Gate Characteristics

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#### **ORDERING INFORMATION TABLE**



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2 - Module type

- Circuit configuration (see Circuit Configuration table)

Current code (105 A)

Voltage code (see Voltage Ratings table)

#### Note

To order the optional hardware go to <u>www.vishay.com/doc?95172</u>

CIRCUIT CONFIGURATION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs doubler circuit	Т	VSKT (1)  (1)  (2)  (2)  (3)  (6)  (7)  (6)  (7)  (7)  (8)  (9)  (9)  (1)  (1)  (1)  (1)  (1)  (2)  (3)  (4)  (7)  (6)  (7)  (6)
SCR/diode doubler circuit, positive control	Н	VSKH 1 (2) (2) (3) (3) (4) (6) (4) (6)
SCR/diode doubler circuit, negative control	L	VSKL (1)-  1 (2)-  (2)-  (3)-  (3)-  (4)-  (5)-  (6)-  (7) (6)
SCR/diode common anodes	N	VSKN 1

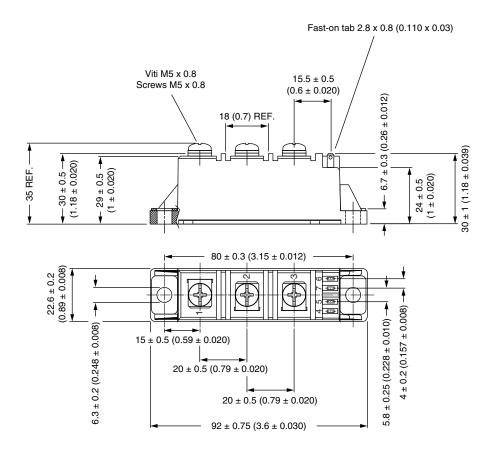
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95368				



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# **ADD-A-PAK Generation VII - Thyristor**

#### **DIMENSIONS** in millimeters (inches)





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VSKT105/12S90P VSKT106/14P VSKL105/10P VSKL105/14P VSKH105/08P VSKH105/06P VSKL105/08P

VSKT105/06P VSKT105/08P VSKL105/06P VSKT105/16S90P VSKH105/16S90P VSKH105/04S90P VSKT105/14P

VSKH105/12P VSKH105/12S90P VSKH105/14P VS-VSKH105/16 VS-VSKH105/04 VS-VSKH105/14 VS
VSKH105/12 VS-VSKL105/08 VS-VSKL105/06 VS-VSKT105/12 VS-VSKL105/14 VS-VSKL105/04 VS-VSKT105/10

VS-VSKT105/08 VS-VSKN105/16 VS-VSKT105/14 VS-VSKT105/16 VS-VSKL105/12 VS-VSKT105/06 VS
VSKL105/10 VS-VSKH105/08 VS-VSKL105/16 VS-VSKH105/06 VS-VSKT105/04 VS-VSKN105/04 VS
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